

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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OPB732, OPB732WZ



Features:

- PC board mounting (OPB732)
- 24" (610 mm) 26 AWG wired with mounting tabs (OPB732WZ)
- Non-contact infrared switch
- Up to 1" or more reflective distance depending on circuitry



Description:

OPB732 uses an Infrared LED and Phototransistor in a reflective switch configuration. The assembly is offered with either PCBoard through hole pins (**OPB732**) or 24" (610 mm), 26 AWG wires (**OPB732WZ**), and uses an opaque housing to reduce the sensor's ambient light sensitivity. The emitter and sensor are protected by a clear window, providing a device that can operate in a dusty environment. The phototransistor can be configured as a Common Collector or Common Emitter device.

While an object is in the reflective path of the device, light from the LED will be reflected back to the housing irradiating the surface (base) of the phototransistor. When Infrared light strikes the phototransistor, the transistor becomes forward biased and is considered to be in the "ON" state, providing an $I_{C(ON)}$ current proportional to the light striking the phototransistor. With the Infrared light from the LED not being reflected to the phototransistor, the phototransistor turns "OFF," minimizing the $I_{C(ON)}$ current.

Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- · Assembly line automation
- Machine automation
- Equipment security
- Door sensor
- Machine safety
- End of travel sensor

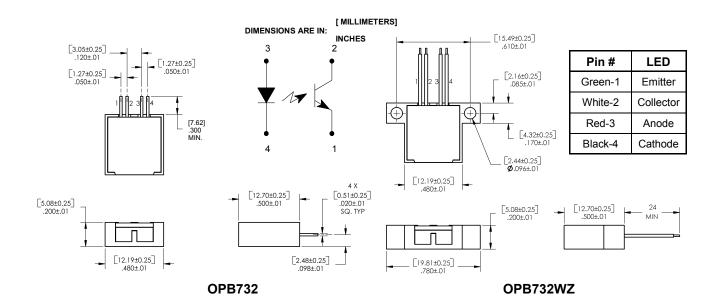
Ordering Information					
Part Number	LED Peak Wavelength	Lead Length / Spacing			
OPB732	850 nm	0.150"/ see diagram			
OPB732WZ	830 1111	24" / 26 AWG Wire			



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Electrical Specifications

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Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)							
Storage Temperature						-40° C to +100° C	
Operating Temperature						-40° C to +85° C	
Lead Soldering Temperature (1/16" (1.6mm) from case for 5 seconds with soldering iron) ⁽²⁾						260° C	
LED							
Forward Current						50 mA	
Peak Forward current (2 μs pulse width, 0.1% Duty Cycle)					1 A		
Reverse DC Voltage					3 V		
Power Dissipation					100 mW		
Output Photo Transistor							
Collector-Emitter Voltage					30 V		
Collector DC Current						50 mA	
Power Dissipation						100 mW	
Electrical Characteristics (T _A = 25° C unless otherwise noted)							
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TES	T CONDITIONS
Input LED (See OP265 for additional information, reference only)							

Electrical Characteristics (T _A = 25° C unless otherwise noted)								
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS		
Input LED (See OP265 for additional information, reference only)								
V _F	Forward Voltage	-	-	1.8	V	I _F = 20 mA		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V		
Output Phototransistor (See OP505 for additional information, reference only)								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_C = 100 \mu\text{A}, E_E = 0 \text{mw/cm}^2$		
I _{CEO}	Collector-Emitter Dark Current	-	-	100	nA	$V_{CE} = 10 \text{ V, } E_E = 0 \text{ mw/cm}^2$		
Coupled								
V _{CE(SAT)}	Collector-Emitter Saturation Voltage ⁽⁴⁾	-	-	0.4	V	$I_C = 250 \mu\text{A}, I_F = 30 \text{mA}$, (4)		
I _{C(ON)}	On-State Collector Current ⁽⁴⁾	0.25	-	-	mA	$V_{CE} = 1 V, I_F = 30 mA, (4)$		
I _{cx}	Cross Talk	-	-	50	μΑ	$V_{CE} = 5 \text{ V, } I_F = 30 \text{ mA,}$ No reflective surface		

Notes:

- (1) All parameters tested using pulse technique.
- (2) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- (3) Methanol or isopropanol are recommended as cleaning agents. The plastic housing is soluble in chlorinated hydrocarbons and keytones.
- (4) Distance = 1" (from front of package to a 90% diffuse reflective white card)

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